

# Process Flow of XXX XXX XXX

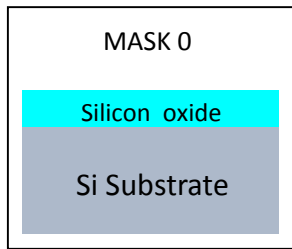
Project:

Name:

Substrate:

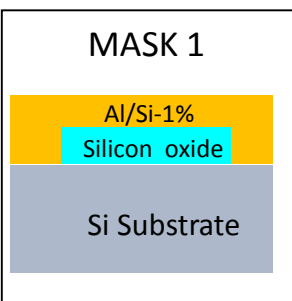
Date:

Cross-section



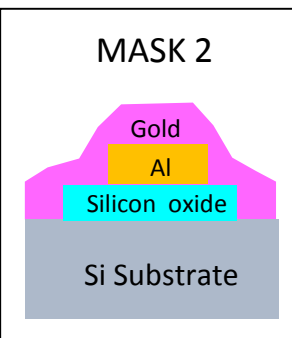
Wafer Cleanliness
Clean
Clean
Clean
Clean

Step No.	Equipment	Location	Cleanliness	Process	Requirements
0.1	A3: Sulfuric Cleaning	P201000	Clean	Initial Clean	H2SO4 + H2O2, 10mins, 120C
0.2	A2: HF:H2O (1:50)	P201000	Clean	HF dip	1 min
0.3	Spin Dryer-A	P201000	Clean	Dry the wafer automatically	
0.4	Diff. Furnace-D2 Dry/Wet Oxidation	P201000	Clean	Sacrificial Oxide Growth	200A



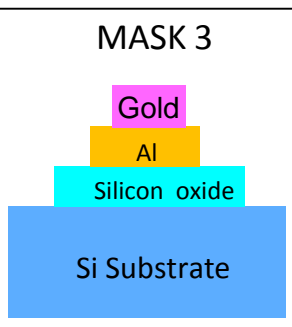
Wafer Cleanliness
Clean
Clean
Clean
Clean
Clean
Clean
Clean
Clean
Clean
Semi-Clean

Step No.	Equipment	Location	Cleanliness	Process	Requirements
1.1	B1: Sulfuric Cleaning	P201000	Clean	Standard Cleaning	10mins, 120C
1.2	Spin Dryer-B	P201000	Clean	Dry the wafer automatically	
1.3	SVG88 Coater Track	P200100	Clean/Semi-Clean	HMDS, PR coating, soft bake	HPR504, 1.2µm, soft bake: 110C 1min
1.4	Karl Suss MA6 #2	P200100	Clean/Semi-Clean	Define oxide pad	5s
1.5	SVG88 Developer Track	P200100	Clean/Semi-Clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120C, 1min
1.6	C3: BOE	P201000	Clean	Oxide Etch	20s
1.7	E4: Resist Strip	P201000	Clean/Semi-Clean	Sulfuric resist strip	H2SO4 + H2O2, 120C, 10mins
1.8	Spin Dryer-E	P201000	Clean/Semi-Clean	Spin dry	
1.9	Varian 3180 Sputter	P201000	Semi-Clean	Aluminum Sputtering	4000A



Wafer Cleanliness
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Semi-Clean
Non-Standard

Step No.	Equipment	Location	Cleanliness	Process	Requirements
1.1	D1: Dump rinse	P201000	Semi-Clean	Wafer cleaning	4 cycles
1.2	Spin Dryer-D	P201000	Semi-Clean	Dry the sample	
1.3	SVG88 Coater Track	P200100	Clean/Semi-Clean	HMDS, PR coating, soft bake	HPR504, 1.2µm, soft bake: 110C 1min
1.3	Karl Suss MA6 #2	P200100	Clean/Semi-Clean	Al Patterning	4.5s
1.4	SVG88 Developer Track	P200100	Clean/Semi-Clean	Develop and hard bake	1min, hard bake: 120C 1min
1.6	IPC 3000 Asher #2	P201000	Semi-Clean	Descum	70C, 1min
1.7	D1: Aluminum Etch	P201000	Semi-Clean	Al etch	1.5min
1.8	D: Freckle Etch	P201000	Semi-Clean	Remove Silicon Residue	1min
1.9	Spin Dryer-D	P201000	Semi-Clean	Spin dry	
1.10	Y1: MS2001	P200100	Semi-Clean	Resist Stripping	5mins, 70C
1.11	Spin Dryer-Y	P200100	Semi-Clean	Spin dry	
1.12	ARC-12M Sputter	P201000	Non-Standard	Gold Sputtering	500A



Wafer Cleanliness
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard
Non-Standard

Step No.	Equipment	Location	Cleanliness	Process	Requirements
2.1	F1: dump rinse	P201000	Non-Standard	Cleaning	500A
2.2	Spin Dryer-F	P201000	Non-Standard	Spin Dry	
2.2	HMDS Primer #1	P200100	Non-Standard	HMDS Priming	10mins
2.3	SUSS Coater	P200100	Semi-Clean/Non-Standard	Resist Coating	HPR504, 1.2µm
2.4	Hot Plate-C	P200100	Non-standard	Soft bake	1min 110C
2.5	AB-M Aligner #2 (UV)	P200100	Semi-Clean/Non-Standard	Photo patterning	6s
2.6	W2: FHD-5	P200100	Non-Standard	Develop & Rinsing	1min
2.7	Spin Dryer-W	P200100	Non-Standard	Spin dry	
2.8	Shellab (120C)	P200100	Non-standard	Hard bake	120C, 30mins
2.9	Wet-station F	P201000	Non-standard	Gold etching with KI Solution	Use a separate container
2.10	Spin Dryer-F	P201000	Non-Standard	Spin dry	
2.11	W1: MS2001 Resist Strip	P200100	Non-standard	Resist Stripping	70C 5mins
2.12	W: N2 gun	P200100	Non-standard	Dry the samples using N2 gun	

Signature of Supervisor: